

(93) ((channel with ((bl bitline bit adj line 1)
(25085) first adj Gate
(25613) second adj Gate
(892216) charge
(45481) charge adj stor \$4
(95402) ono
(345908) nitride ono
(595) (nitride ono) near4 (charge adj stor \$4)
(11094) (first adj Gate) near9 (second adj Gate)
(78) (((first adj Gate) near9 (second adj Gate)) near6 ((perpendicular \$2 orthogonal \$3))
(0) (((first adj Gate) near9 (second adj Gate)) near6 ((perpendicular \$2 orthogonal \$3))
(182) (((first adj Gate) near9 (second adj Gate)) with ((perpendicular \$2 orthogonal \$3))
(0) (((first adj Gate) near9 (second adj Gate)) with ((perpendicular \$2 orthogonal \$3))
(0) (((first adj Gate) near9 (second adj Gate)) with ((perpendicular \$2 orthogonal \$3))
(13) (((first adj Gate) near9 (second adj Gate)) with ((perpendicular \$2 orthogonal \$3))
(187) two adj (charge adj stor \$4)
(3) ((channel with ((bl bitline bit adj line 1)
(206) (punch adj through) adj region
(31) ((channel with ((bl bitline bit adj line 1)
(35) ((punch adj through) adj region) and ((nitride ono) near4 (charge adj stor \$4))
(3) ((sonos monos) ono) same ((punch adj through) adj region)
(41) ((sonos monos) ono) and ((punch adj through) adj region)
(6) ((sonos monos) ono)

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Tagged (13)

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DBs: USPAT:US PGPUB: EPO: JPO: DERIVENT: IBM: TDO
Default operator: OR

Plurals

Highlight all hit terms initially

((channel with ((bl bitline bit adj line 1)
) and ((Gate adj (dielectric insulat \$4)) near4 nitride) and ((sonos monos) ono
) ((second with (first adj ((control adj (gate electrode) CG)
) with ((perpendicular \$2 orthogonal \$3)
) and ((sonos monos) ono
)

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	U	T	Inventor	Document#	Issue #	Title	Current	Current XR	Retrieval	S	C	P	Image	Doc	P
1			Harari, Elijah	US 2003010	20030:3	Multi-state non-volatile integrated circuit me	438/200:257/E21.68							US 200301	
2			Kamigaki, Yo	US 6674122	20040:8	Semiconductor integrated circuit	257/326:257/324;							US 667412	
3			Fujiwara, Ichi	US 8674120	20040:4	Nonvolatile semiconductor memory device a	257/324:257/318;							US 867412	
4			Shukuri, Shoji	US 2003019	20031:9	Semiconductor integrated circuit device and	365/185;							US 200301	
5			Sugita, Yasuh	US 2002004	20020:2	Nonvolatile semiconductor memory device, p	365/200;							US 200200	
6			Fujiwara, Ichi	US 8717860	20040:3	Method of erasing non-volatile semiconducto	365/185:365/185.29;							US 871786	
7			Eitan, Boaz	US 6566689	20030:2	Non-volatile electrically erasable and progre	257/296:257/390;							US 656689	
8			Kobayashi, T	US 6563728	20030:2	Semiconductor memory device and method f	365/63 :257/E21.67							US 656372	
9			Sugita, Yasuh	US 6531732	20030:2	Nonvolatile semiconductor memory device, p	257/315:257/316;							US 653173	
10			Fujiwara, Ichi	US 6434053	20020:5	Nonvolatile semiconductor memory device a	365/185:257/324;							US 643405	